

## N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
30	0.008 at $V_{GS} = 10$ V	13	6.1 nC
	0.011 at $V_{GS} = 4.5$ V	11	

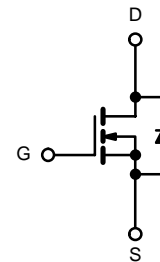
### FEATURES

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFET
- Optimized for High-Side Synchronous Rectifier Operation
- 100 %  $R_g$  Tested
- 100 % UIS Tested


**RoHS**  
 COMPLIANT

### APPLICATIONS

- Notebook CPU Core
- High-Side Switch



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	$I_D$	13	A
	$T_C = 70$ °C		10	
	$T_A = 25$ °C		$g^{b, c}$	
	$T_A = 70$ °C		$7^{b, c}$	
Pulsed Drain Current		$I_{DM}$	45	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	$I_S$	3.7	
	$T_A = 25$ °C		$2.0^{b, c}$	
Single Pulse Avalanche Current	$L = 0.1$ mH	$I_{AS}$	20	mJ
Avalanche Energy		$E_{AS}$	21	
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	4.1	W
	$T_C = 70$ °C		2.5	
	$T_A = 25$ °C		$2.2^{b, c}$	
	$T_A = 70$ °C		$1.3^{b, c}$	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$t \leq 10$ s	$R_{thJA}$	39	55	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	25	29	

Notes:

 a. Base on  $T_C = 25$  °C.

b. Surface Mounted on 1" x 1" FR4 board.

 c.  $t = 10$  s.

d. Maximum under Steady State conditions is 85 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		26		mV/ $^{\circ}\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.008		$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 9\text{ A}$		0.011		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		50		S
Dynamic <sup>b</sup>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		800		pF
Output Capacitance	$C_{oss}$			165		
Reverse Transfer Capacitance	$C_{rss}$			73		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		15	23	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 10\text{ A}$		6.8	10.2	
Gate-Source Charge	$Q_{gs}$			2.5		
Gate-Drain Charge	$Q_{gd}$			2.3		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.36	1.8	3.6	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.4\text{ }\Omega$ $I_D \cong 9\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		16	23	ns
Rise Time	$t_r$			12	16	
Turn-Off Delay Time	$t_{d(off)}$			16	22	
Fall Time	$t_f$			10	18	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.4\text{ }\Omega$ $I_D \cong 9\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		8	16	
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			16	22	
Fall Time	$t_f$			8	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^{\circ}\text{C}$			10	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				50	
Body Diode Voltage	$V_{SD}$	$I_S = 9\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^{\circ}\text{C}$		15	30	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			6	12	nC
Reverse Recovery Fall Time	$t_a$			8		ns
Reverse Recovery Rise Time	$t_b$			7		

Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

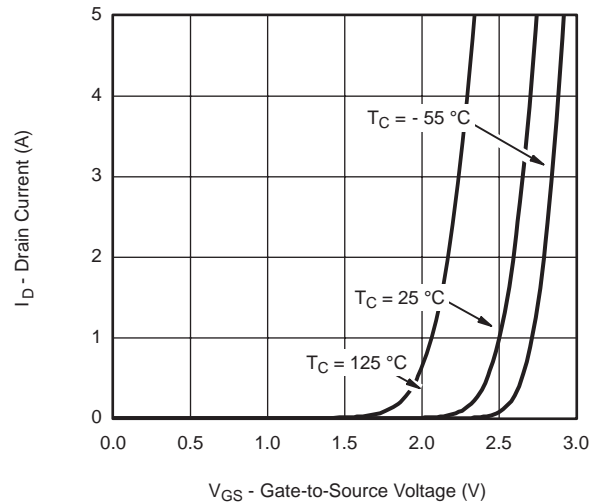
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

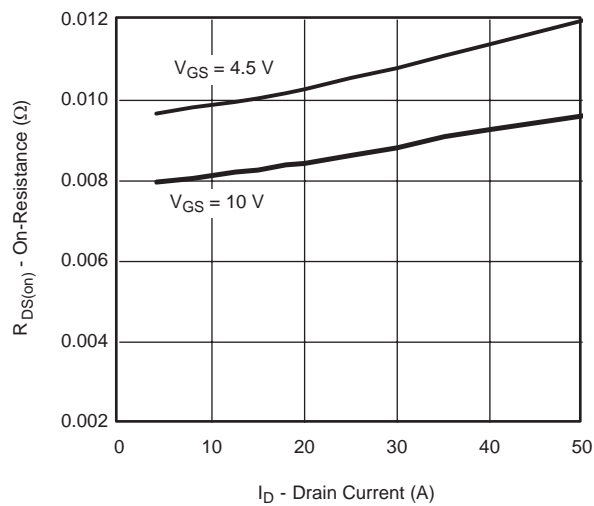
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



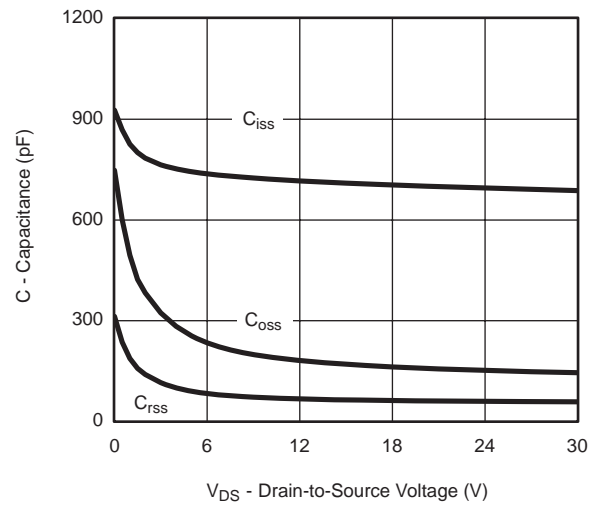
Output Characteristics



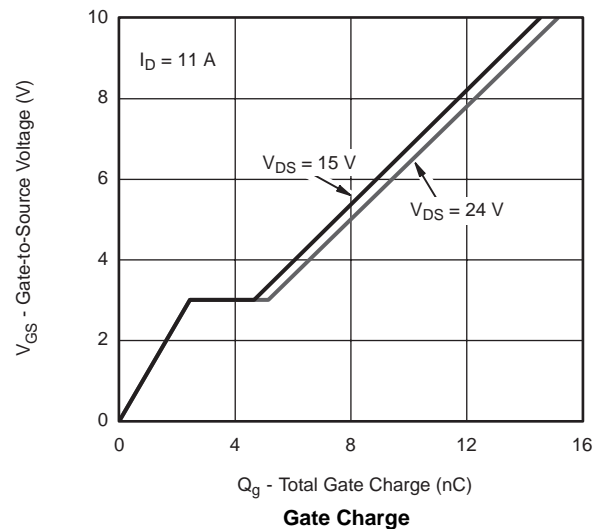
Transfer Characteristics



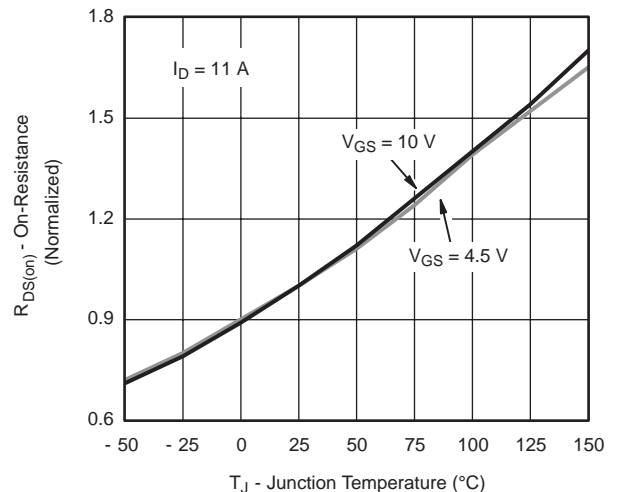
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

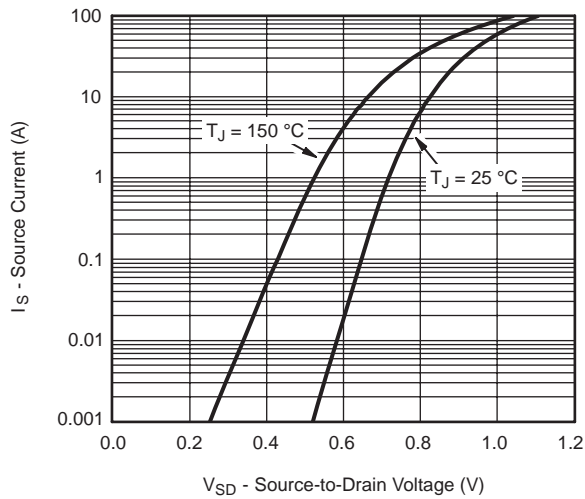


Gate Charge

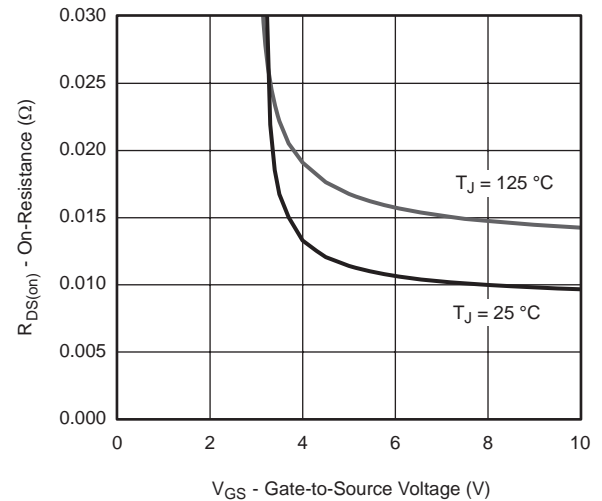


On-Resistance vs. Junction Temperature

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



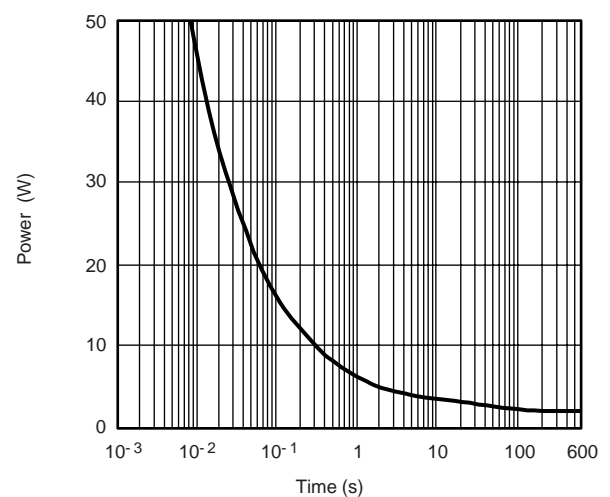
Source-Drain Diode Forward Voltage



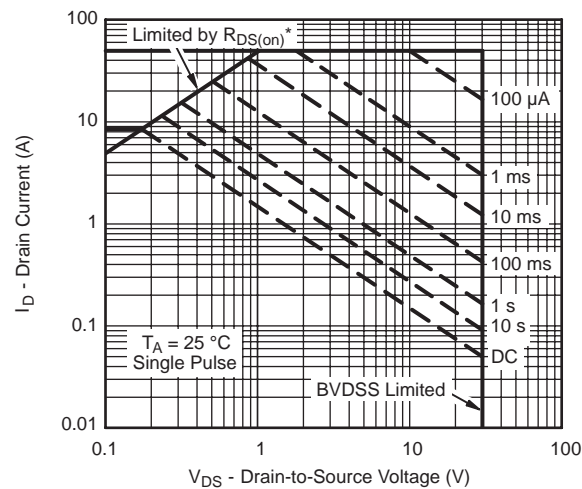
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



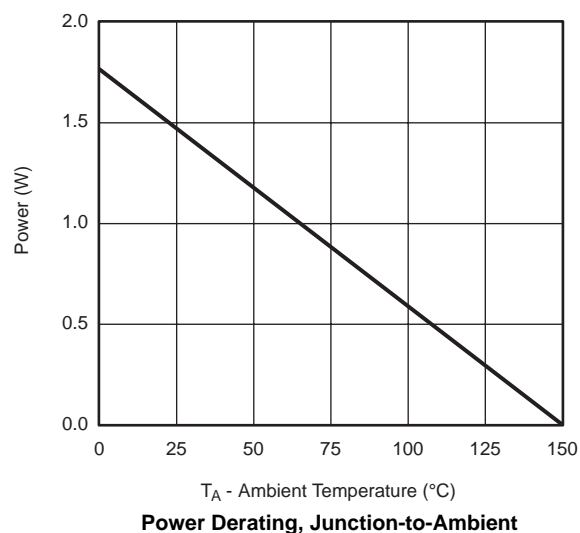
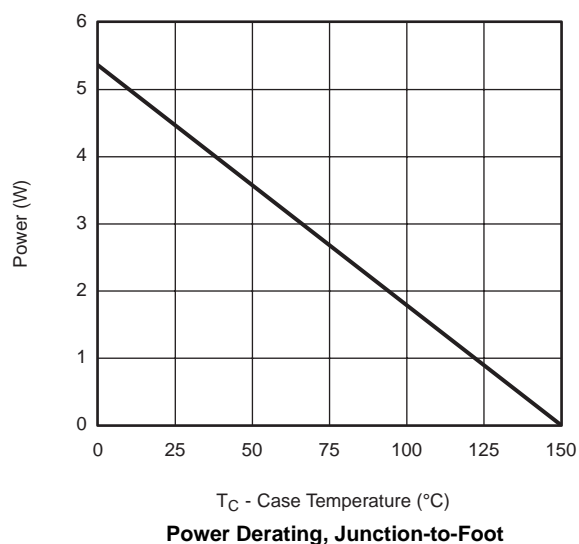
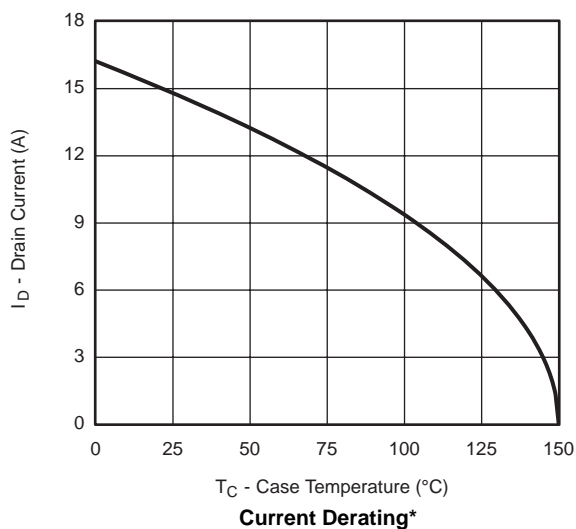
Single Pulse Power, Junction-to-Ambient



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

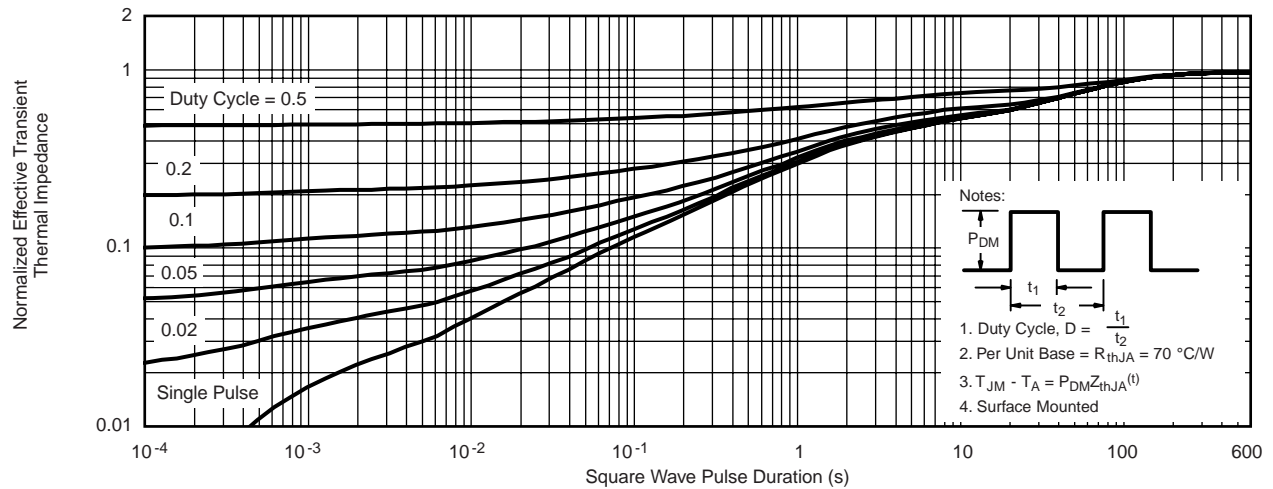
Safe Operating Area, Junction-to-Ambient

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

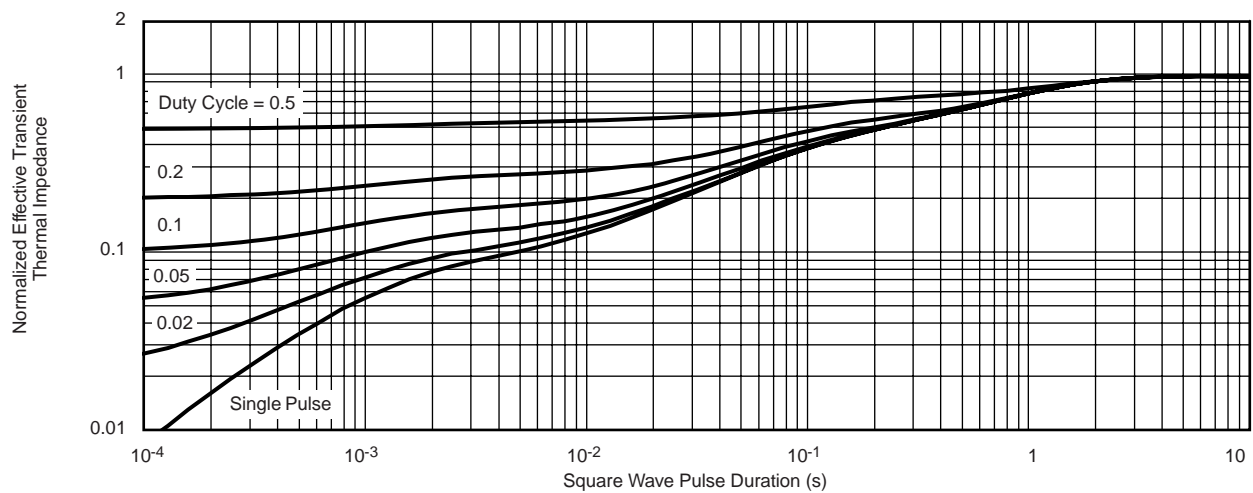


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

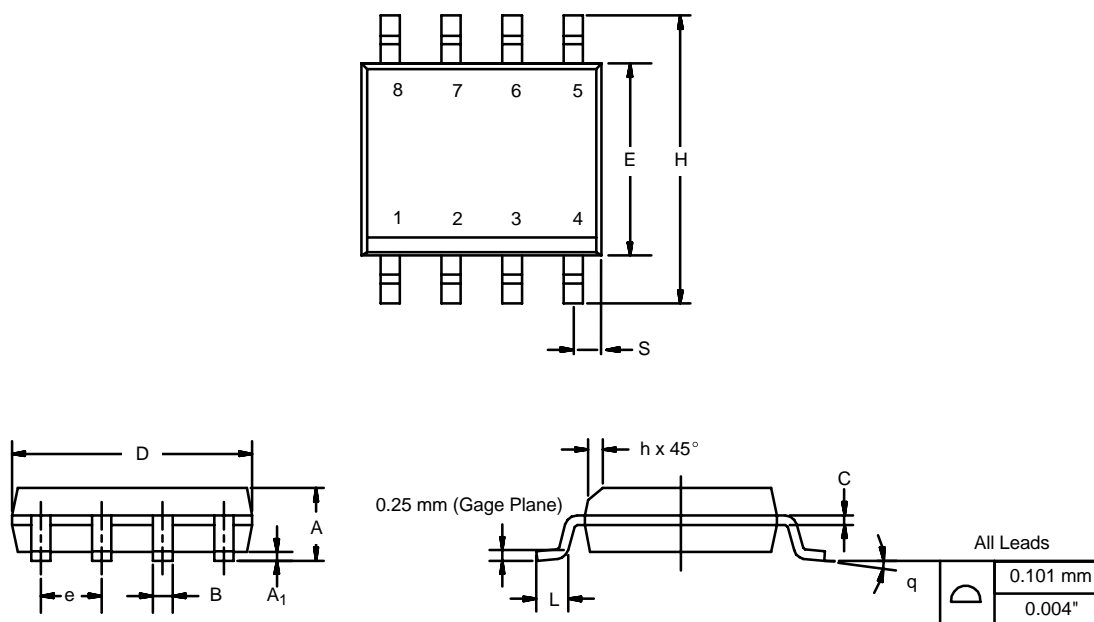


**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

## SOIC (NARROW): 8-LEAD



## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)



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